

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: kiyoshi IRINO

Serial No.: Divisional of SN 08/917,936

Art Unit: Not Yet Assigned

Filed: Herewith

Examiner: Not Yet Assigned

For: METHOD OF FABRICATING A SEMICONDUCTOR
DEVICE CONTAINING NITROGEN IN A GATE OXIDE
FILM (As Amended)

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

October 27, 1999

Sir:

Prior to examination on the merits, please amend the above-identified application as follows:

IN THE TITLE:

Please amend the title to read:

--METHOD OF FABRICATING A SEMICONDUCTOR DEVICE
CONTAINING NITROGEN IN A GATE OXIDE FILM--.

IN THE CLAIMS:

Please cancel claims 1-5 and 14.

REMARKS

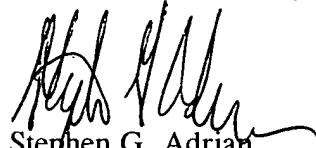
Claims 6-13 are pending. The above amendments are believed to place the application in better condition for examination.

Prompt and favorable action on the merits is earnestly solicited.

In the event any fees are required in connection with this paper, please charge Deposit
Account No. 01-2340.

Respectfully submitted,

ARMSTRONG, WESTERMAN, HATTORI,
McLELAND & NAUGHTON



Stephen G. Adrian
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